

WR0<5 ММ Ё QSQ Æ М ы s ll 1 Silicon NPN transistor in a TO-92 Plastic Package.

х ѿ з і лъ 5VD4<;4 й ´
High h_{FE} , complementary pair with 2SA1981.

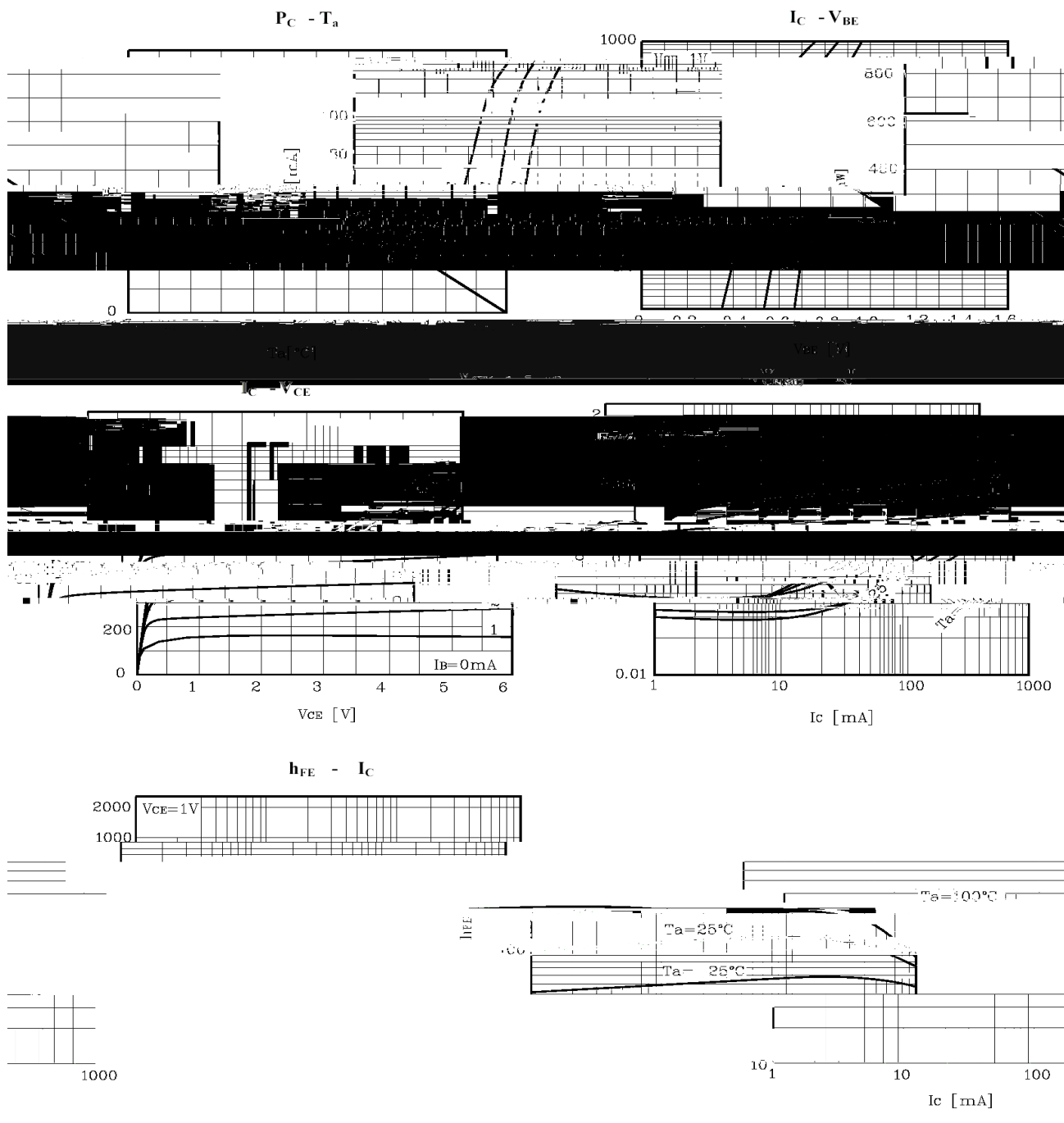
ххх _ л і ' ѿ з
Audio power amplifier application.



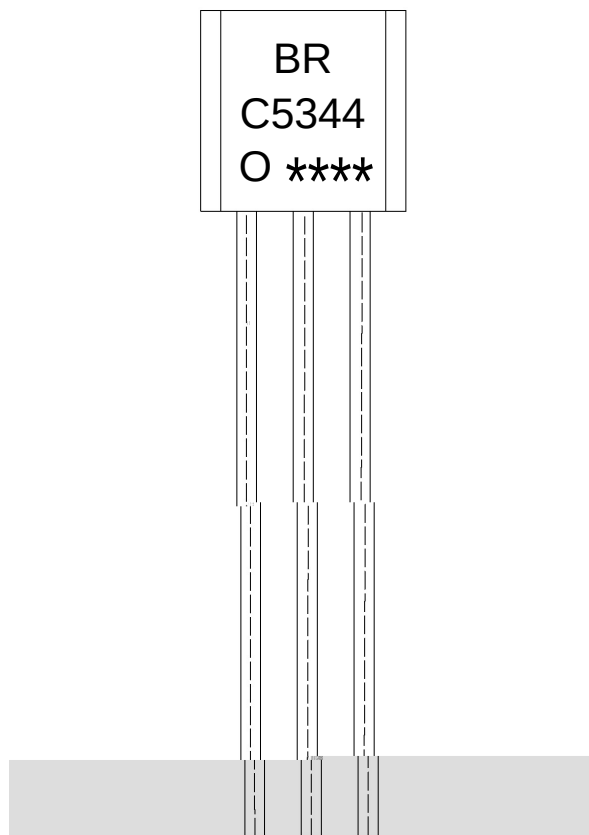
PIN1 х Base PIN 2 х

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	35	V
Collector to Emitter Voltage	V_{CEO}	30	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current - Continuous	I_C	800	mA
Collector Power Dissipation	P_C		

/ **Electrical Characteristic Curve**



/ Marking Instructions



б " X

EU:

№ 3^И ПД

F8677 X

№ 3^И ПД

R:

№ k_И^с 6 ПД

---- X

№ 1 F ПД^И 1 F ПД^И Ψ P

Note:

BR:

Company Code.

C5344:

Product Type.

R:

h_{FE} Classifications Symbol.

****:

Lot No. Code,code change with Lot No.

() / Temperature Profile for Dip Soldering(Pb-Free)



б " X

1. 1. 25~150 °C, Time: 60~90sec;
2. 2. 255 °C, Duration: 5 ° 0.5sec;
3. 3. Cooling Speed: 2~10 ° /sec.

Note:

1. Preheating: 25~150 °C, Time: 60~90sec.
2. Peak Temp.: 255 °C, Duration: 5 ° 0.5sec.
3. Cooling Speed: 2~10 ° /sec.

/ Resistance to Soldering Heat Test Conditions

270 ± 5 10 ± 1 sec. Temp: 270±5 Time: 10±1 sec

/ Packaging SPEC.

“Q T Y E / BULK

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm3)		
	Units/Bag 只/袋	Bags/Inner Box 袋/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Bag 袋	Inner Box 盒	Outer Box 箱
TO-92	1,000	10	10,000	5	50,000	135×190	237×172×102	560×245×195
	1,000	10	10,000	10	100,000	135×190	237×172×102	560×245×375

“V Y E / AMMO

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm3)	
	Units/tape 只/纸带	Tape/Inner Box 纸带/盒	Rows/Inner Box 纸带层/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Inner Box 盒	Outer Box 箱
TO-92	3,000	1	120	10	30,000	328×230×42	小箱 480×346×235, 大箱 547×407×268

/ Notices